

PRELIMINARY AMENDMENT
New U.S. Patent Application

AMENDMENTS TO THE SPECIFICATION

Please add the following new Abstract of the Disclosure:

A multilayer wiring structure for connecting a semiconductor device is disclosed which is obtained by forming metal wirings on a substrate in which the semiconductor device is formed. The wiring structure is free from such conventional problems that insulation between wirings next to each other is damaged or insulation resistance between wirings next to each other is deteriorated by generation of leakage current when fine metal wirings are formed in a porous insulating film. A method for producing such a wiring structure is also disclosed. In the metal wiring structure on the substrate in which the semiconductor device is formed, a insulating barrier containing an organic matter is formed between an interlayer insulating film and a metal wiring. This insulating barrier layer reduces leakage current between wirings next to each other, thereby improving insulation reliability.